



STM7822

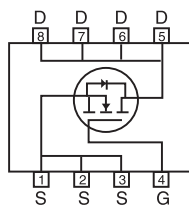
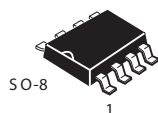
N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (m Ω) Max
25V	14A	6.5 @ V _{GS} = 10V
		7.5 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V _{spike} ^d	30	V
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	±16	V
Drain Current-Continuous ^a @ T _c =25°C -Pulsed ^b	I _D	14	A
	I _{DM}	56	A
Drain-Source Diode Forward Current ^a	I _S	14	A
Maximum Power Dissipation ^a	P _D	2.5	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θ JA	50	°C/W
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STM7822

ELECTRICAL CHARACTERISTICS (TA=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	25			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±16V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250uA	0.7	1.0		V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D = 14A			6.5	m ohm
		V _{GS} =4.5V, I _D = 10A			7.5	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	10			A
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 14A		20		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} =16V, V _{GS} = 0V f =1.0MHz		3725		pF
Output Capacitance	C _{OSS}			663		pF
Reverse Transfer Capacitance	C _{RSS}			494		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 16V, I _D = 14A, V _{GS} = 5V, R _{GEN} = 6 ohm		18.1		ns
Rise Time	t _r			6.5		ns
Turn-Off Delay Time	t _{D(OFF)}			26.8		ns
Fall Time	t _f			17.1		ns
Total Gate Charge	Q _g	V _{DS} =16V, I _D =14A,V _{GS} =10V		87.4		nC
		V _{DS} =16V, I _D =14A,V _{GS} =5V		45.2		nC
Gate-Source Charge	Q _{gs}	V _{DS} =16V, I _D = 14A, V _{GS} =5V		10		nC
Gate-Drain Charge	Q _{gd}			14.3		nC

STM7822

ELECTRICAL CHARACTERISTICS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =14A		0.84	1.2	V

Notes

- a.Surface Mounted on FR4 Board, t≤10sec.
- b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle≤ 2%.
- c.Guaranteed by design, not subject to production testing.
- d.Guaranteed when external R_g=6 ohm and t_f < t_f max

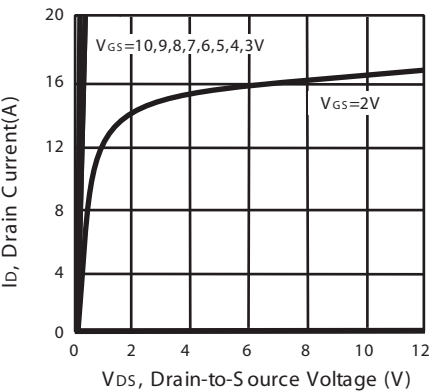


Figure 1. Output Characteristics

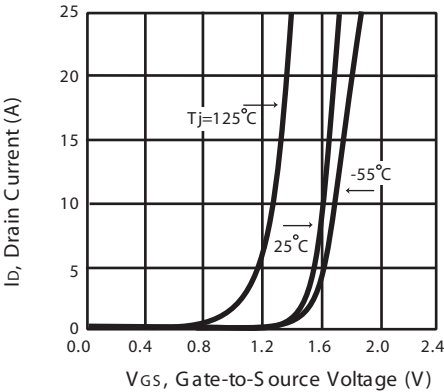


Figure 2. Transfer Characteristics

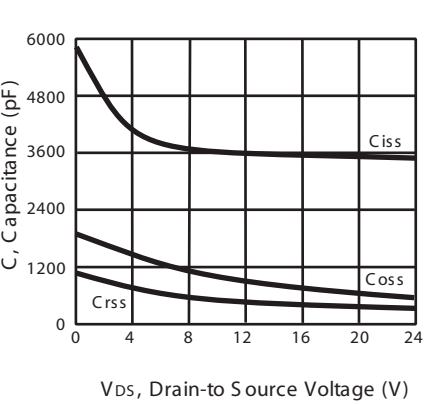


Figure 3. Capacitance

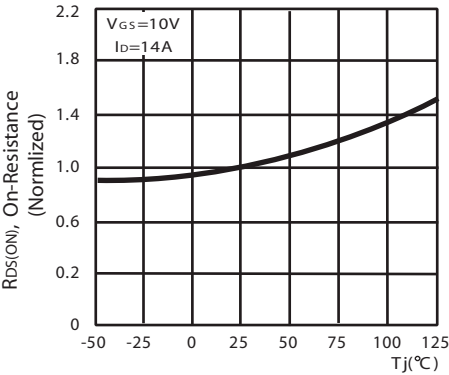
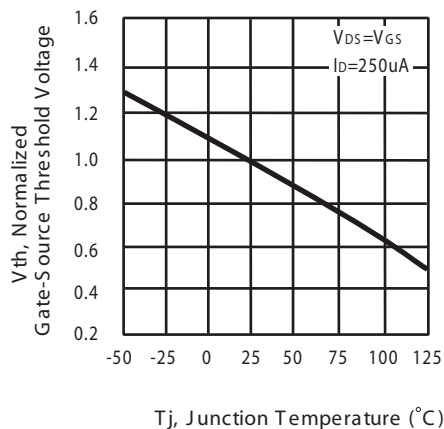


Figure 4. On-Resistance Variation with Temperature

STM7822



with Temperature

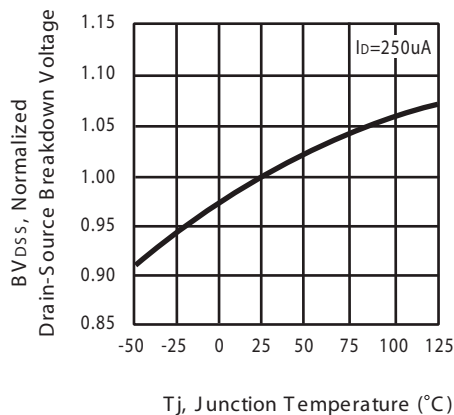


Figure 6. Breakdown Voltage Variation with Temperature

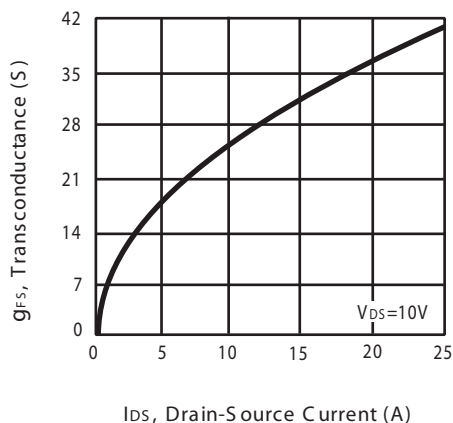


Figure 7. Transconductance Variation with Drain Current

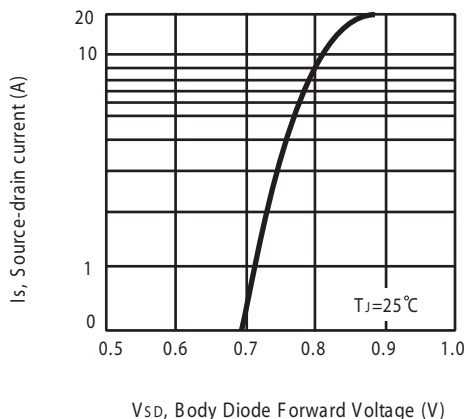


Figure 8. Body Diode Forward Voltage Variation with Source Current

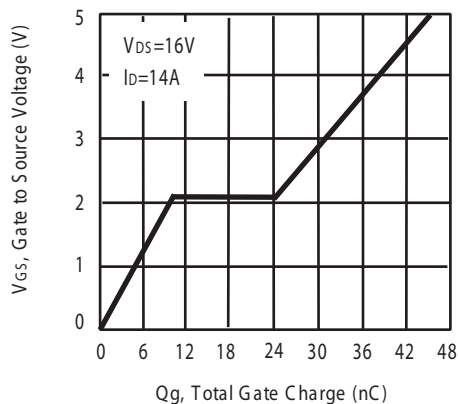


Figure 9. Gate Charge

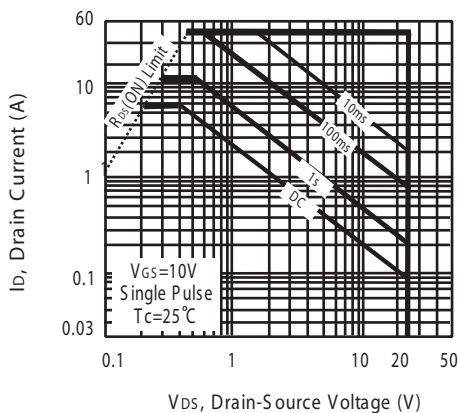


Figure 10. Maximum Safe Operating Area

STM7822

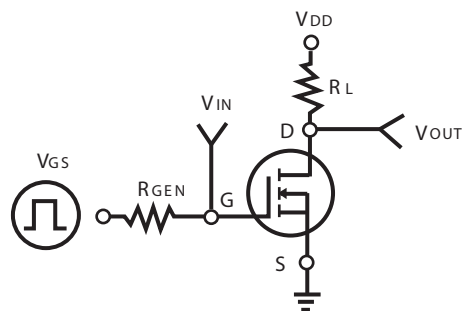


Figure 11. Switching Test Circuit

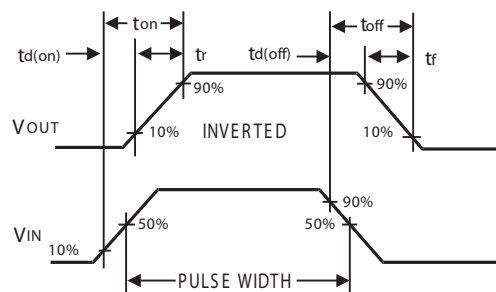


Figure 12. Switching Waveforms

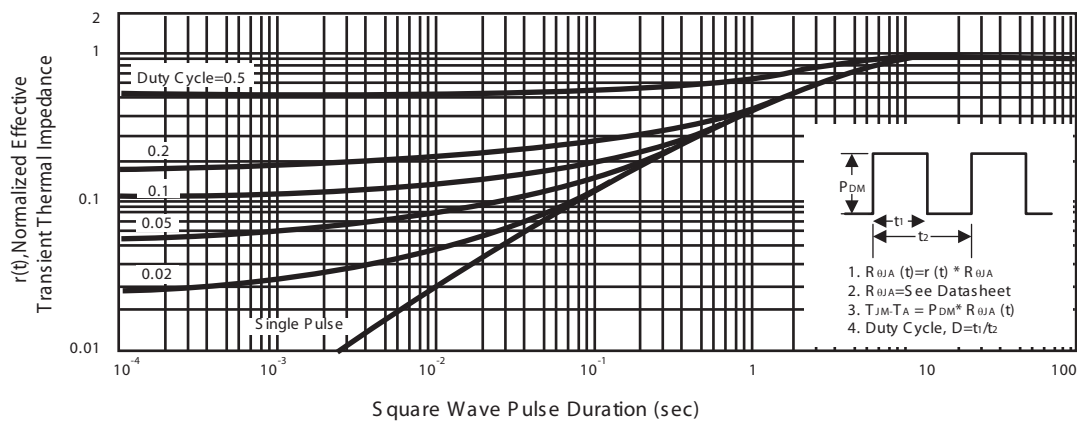
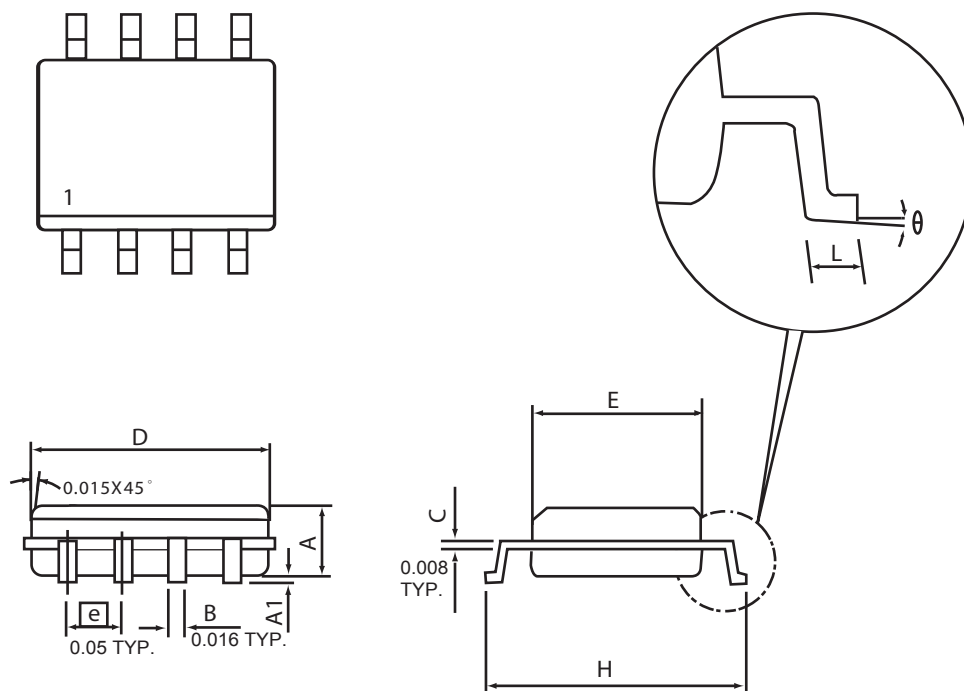


Figure 13. Normalized Thermal Transient Impedance Curve

STM7822

PACKAGE OUTLINE DIMENSIONS

SO-8

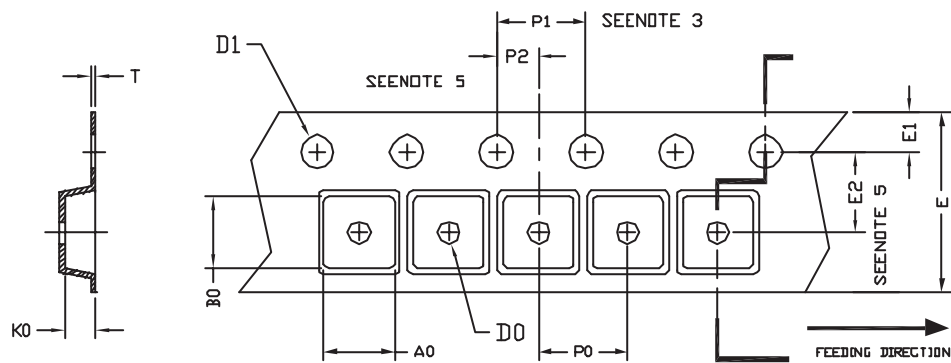


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

STM7822

SO-8 Tape and Reel Data

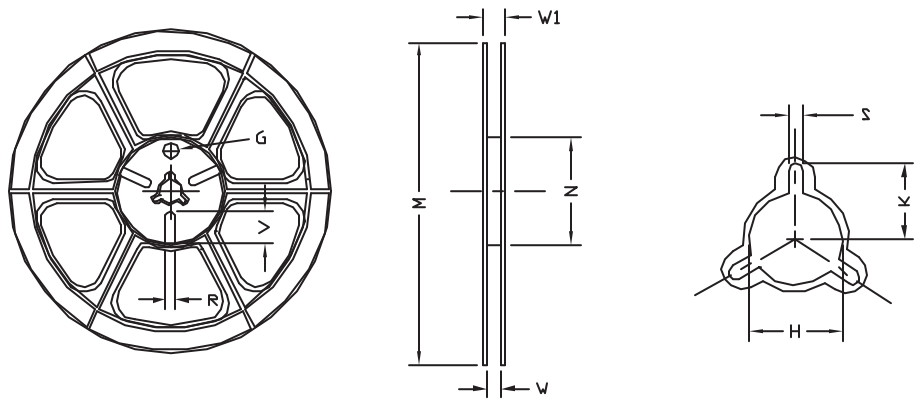
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 ± 0.15	---	---	---